

# Power transfer by non radiative electromagnetic fields between high Q resonant coupled circuits

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Between two high quality-factor (Q) resonant magnetically coupled circuits, non-radiative power transfer is modelled and observed, in agreement with predictions found in recent works from MIT. The physical behaviour of the receptor as well as the geometry of the power flux lines (Poyting) are explained in terms of general behaviour of the power flux near completely absorbing targets. Practical consequences are extracted and generalisations of the source-receptors' geometries are proposed.